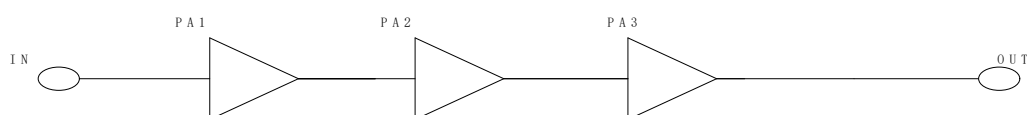


0.02-6G SSPA-300W

1 FEATURES

- ✓ GaN HEMT Device
- ✓ High power
- ✓ High efficiency
- ✓ CW output
- ✓ Direct current supply
- ✓ 0.02-0.5G,0.5-3G,3-6G

2 Schematic diagram



3 SPECIFICATIONS

GaN CW High Power Amplifier

Raw	Parameter	Value	unit	Comments
1	Frequency range	0.02-0.5G,0.5-3G,3-6G	GHz	
2	Output Power	55	dBm	
3	Working Mode	CW		TTL
4	Spurious Level	55	dBc	
5	Input Power	0±2	dBm	
6	Efficiency	>25	%	
7	Input VSWR	1.5:1	-	
8	input Connector	SMA-KFD50	-	
9	Output Connector	N-KFD50	-	
10	Temp Range	-20~+55	degree	
11	Supply	+28	V	

The product needs to be installed on a cold plate for contact heat dissipation.

Connector definition

P(0.02-0.5G)

A1	A2	A3	1	2	3	4	5	6	7
+36V	+36V	+36V	NC	NC	NC	NC	NC	Enable	Bit
A4	A5	A6							
GND	GND	GND							

P(0.5-3G)

A1	A2	A3	1	2	3	4	5	6	7
+28V	+28V	+28V	NC	NC	NC	NC	NC	Enable	Bit
A4	A5	A6							
GND	GND	GND							

P(3-6G)

A1	A2	A3	1	2	3	4	5	6	7
+28V	+28V	+28V	NC	NC	NC	NC	NC	Enable	Bit
A4	A5	A6							
GND	GND	GND							

Enable: TTL, Turn on at high level

Bit: Normal operation at high level

OUTLINE

